K ondo and anti-K ondo coupling to local m om ents in EuB₆

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W ith a treatment of the 4f states of EuB₆ based on LDA+U method, the mixing of Euf states with B p states around the X point of the B rillouin zone is shown to have unexpected consequences for the e ective exchange interactions. We analyze in detail the orbital character of electronic states close to the Ferm i level and discuss the e ective exchange between the itinerant electrons and the local 4f m om ents. The analysis suggests that the ordered phase m ay provide the rst example of a half metallic sem in etal, and that the physics of EuB₆ should be described in terms of a two band K ondo lattice model with parallel (ferrorm agnetic) coupling of the conduction electrons and antiparallel (antiferrorm agnetic) coupling of the valence electrons to the local 4f m om ents.

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I. IN TRODUCTION

Despite num erous experim ental and theoretical studies, understanding of the electronic properties and m agnetic coupling of EuB₆ still provides challenges. W hile having a simple crystal structure, consisting of a simple cubic lattice of Eu atom swith a B₆ octahedron located in the center of each cubic cell, nevertheless the transport and magnetic properties of this system are complex. EuB₆ orders ferrom agnetically at 15.1 K, which is accom panied by a huge decrease of resistivity and a signi cant blue shift of the re ectivity plasm a edge.¹ At 12.7 K another phase transition takes place, which is observed as a broad peak in the specic heat or an anom aly in the resistivity.² The origin of this transition is still unclear, with possible explanations including spin reorientation³ or a long-wavelength modulation of the spin density. Besides these properties, EuB₆ exhibits a rather sluggish increase of m agnetization with decreasing tem perature⁵ and unusual pressure dependence of the Curie tem perature with strong increase up to 70 kbar and a at dependence at higher pressures.6

The LDA electronic structure of EuB_6 was previously investigated by Hasegawa and Yanase⁷ and Massida et al.⁸ Sm all overlap of conduction and valence bands was found resulting in Ferm isurface pockets centered at the X point of the Brillouin zone. Isostructural C aB₆ and SrB₆ have similar bandstructures, which have seem ed to be consistent with their observed transport properties? (although they are not understood in any detail). Recently CaB₆ has been studied with several variants of the GW m ethod: the conventional pseudopotential GW,¹⁰ and all-electron GW,¹¹ and a self-consistent GW m ethod.¹² W hile there are di ering results among these, the maprity of them predict the opening of a gap of the order of 1 eV, making the LDA conclusions about the groundstate of divalent hexaborides questionable. Recent angle-resolved photoem ission m easurem ents^{13,14} reported a bandgap in CaB₆, and only recently has it been dem onstrated that synthesis from ultrapure boron¹⁵

leads to transport properties that are characteristic of a sem iconductor rather than a sem in etal. For the param – agnetic phase of EuB₆, a bandgap was also observed,¹³ below an occupied electron pocket at the X point that was interpreted as carriers resulting from (a high density of B) vacancies. Recently the transport properties have been interpreted in term s of a sim ilar m odel.¹⁶

A susual in LDA -based band structure calculations of rare earth system s, the 4f states must be treated in a specialway in order to insure their correct lling. In order to enforce the correct lling the 4f states were treated separately from the rest of the system in Ref. 8, neglecting any hybridization involving the f states and thus giving no insight into magnetic coupling mechanisms in EuB_6 . Here we use the LDA + U m ethod, which obtains the correct 4f state lling while keeping these 4f states in the sam e Hilbert space as the rest of the system, and so allows form ixing of 4f states with the valence states. The aim of the present work is to investigate the e ective exchange interaction between the localized f m om ents and the band electrons. For this purpose we perform a detailed analysis of the orbital character and dispersion of the states close to the Ferm i level. Based on this analysis we suggest an unusual two band K ondo lattice m odel to be the relevant picture for understanding the magnetic behavior of $E u B_6$.

II. COMPUTATIONALDETAILS

The calculations were performed using the fullpotential linearized augmented-plane-waves (FLAPW) method as implemented in the Wien2k code.¹⁷ The LDA+U method was used with the double-counting scheme of Anisim ov and collaborators.¹⁸ The standard parametrization of the on-site C oulomb interaction involves two parameters U and J. However, since we are dealing with the Eu²⁺ f⁷ ion, which has completely led spin-up f shell and completely empty spin-down f shell, the role of J reduces to merely renormalizing the U value. Therefore we can set J=0 and quote just the U value. A ll the presented calculations were perform ed w ith LDA exchange-correlation potential in the param eterization of Perdew and W ang.¹⁹ The calculations were perform ed w ithout spin-orbit coupling in the scalar relativistic approximation as implemented of W ien2k code.

The following computational parameters were used. The atom ic radii were 2.7 and 1.5 Bohr for Eu and B respectively. The APW + b basis set²⁰, with additional bcalorbitals for Eu 5s and 5p states, was characterized by plane-wave cut-o $R_m tK_m ax = 7$. We used 56 k-points in 1/48 irreducible wedge of the Brilbuin zone. The numerical convergence of the total energy was better than 0.1 m Ry. The internal parameter was relaxed so that the corresponding force was smaller than 1 m Ry/a.u.

III. RESULTS AND ANALYSIS

A. Bulk properties

W e have perform ed total energy vs. volum e calculations in order to (i) determ ine the theoretical equilibrium volume and bulk modulus and (ii) investigate the in uence of pressure on the band structure. For each value of lattice constant we have optim ized the nearestneighbor B-B distance (the only free internal parameter) using atom ic forces. The calculated energy vs. volum e curve is shown in Fig. 1. The inset shows the scaling of B-B distances with the lattice constant indicating that the bonds within B-octahedra are more rigid than the nearest-neighbor (inter-octahedra) B-B bond. The calculated equilibrium volume of 70.1 A³ is about 96 % of the experim entalvalue.³ The calculated bulk m odulus of 161 GPa is agrees very well with the experimental value.²¹ The present results were obtained with U = 7 eV, however sim ilar calculations perform ed for U = 6, 8, and 9 eV(without optim ization of the internal parameter) showed that the bulk properties are insensitive to the value of U.

B. Bandstructure and exchange coupling

In Fig. 2 we show the spin-polarized bandstructure obtained at the experim ental lattice constant with U=7 eV. Taken literally, the bandstructure indicates a m etallic ground-state with band overlap (negative gap) around X point in both spin channels. M ore importantly the overlap of majority (spin up) bands is strongly enhanced in comparison to m inority (spin down) bands. The origin of the di erent band overlap is the opposite sign of the up/down exchange splitting induced in the conduction and valence band. W hile low ering of the energy of the spin-up conduction band with respect to the spin-down band points to parallel coupling of conduction electrons to the local f m om ents, the energy of the spin-up valence band is higher than that of the spin-down band indicating antiparallel coupling to the local f m om ents. In the

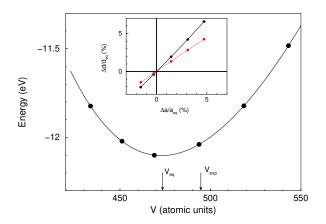


FIG. 1: The total energy vs. volume curve calculated with U = 7eV. In the inset the relative change of the nearest-neighbor (dotted) and intra-octahedron (solid) B {B distance as a function of relative change of the lattice constant.

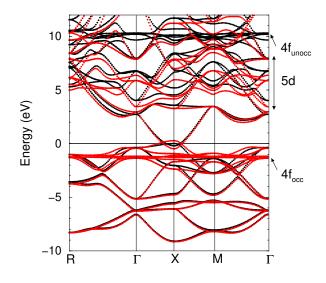


FIG.2: Spin-polarized density band structure obtained with U = 7eV at the experimental lattice constant. The spin-up bands are marked red (brighter).

follow ing we investigate in detail origin of this particular e ective exchange coupling. There are 6 symmetry related X points in the Brillouin zone of simple cubic structure. The follow ing analysis is performed particularly for X = (0,0,1/2) and all references to spatial orientation the orbitals are with respect to this choice. A lso, we do not distinguish between directions in real and k-space, which is not confusing for orthogonal unit cell.

The modulus of the wave-function corresponding to valence band maximum at the X point is shown in Fig. 3. In Fig. 4 we show the schematic plot of the same wave function in terms of B-p and Eu-f orbitals. Let us make several observations: (i) p-orbitals of B atoms at (1/2,1/2,z) do not contribute to this wavefunction while the other B atoms (which lie in the z=1/2 plane) con-

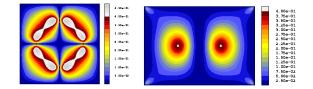


FIG. 3: Contour plot of the absolute value of the m inorityspin valence band wavefunction at the X point. The right panel shows a cut through the boron plane (001) perpendicular to -X direction. The left panel shows a cut by (110) plane going through the center of the unit cell. M ixing with f state in corners of the plot is visible even for the m inority spin. This feature is much stronger for the m a prity spin.

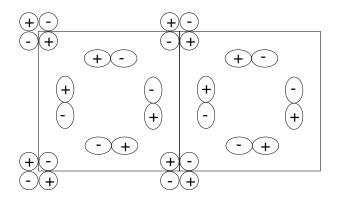


FIG. 4: Schem atic plot of the valence band state at the X point showing the phases of participating orbitals. Two unit cells in X-M direction are shown.

tribute their px or py orbitals, (ii) hybridization between porbitals in the neighboring unit cells (in X-M direction) is forbidden by symmetry at the X point, (iii) dispersion in the -X direction in enhanced by hybridization with Euf orbital of xyz sym metry (note that this hybridization is allowed due to a phase shift of between adjacent Eu layers and thus is forbidden at point). Together points (ii) and (iii) explain the convex dispersion of the valence band with the top at the X point. The hybridization with Euf also explains the antiparallel coupling of the valence electrons to the local f m om ents. The spin up valence orbital hybridizes strongly with the occupied f state localized close to the Ferm i level and thus its energy is increased due to band repulsion. The hybridization shift (level repulsion) in the spin down channel is much weaker and of opposite sign, since the unoccupied f are localized high above the Ferm i level due to the on-site Coulom b repulsion. As a result we obtain an e ective antiferrom agnetic exchange interaction of kinem atic origin in the way described by the periodic Anderson model.²²

Sim ilar analysis is perform ed now for conduction band. By analyzing the orbital contributions to the conduction band we nd that it contains a mixture of B-p and Eu-d states, where the d content decreases when going away from the X point and vanishes at the point. We show

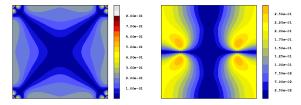


FIG.5: Contour plot of the absolute value of the m inorityspin conduction band wavefunction at the X point. The left panel shows a cut through the Eu plane (001) perpendicular to -X direction. The right panel shows a cut through the center of the unit cell by the (100) plane.

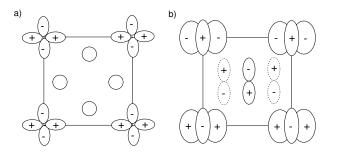


FIG.6: Schematic plot of the conduction band state at the X point showing the phases of participating orbitals. The left panel shows the view along the -X direction. The right panel shows the view along the X-M direction.

the calculated m odulus of the wave-function corresponding to the conduction band at the X point in Fig. 5 and the corresponding schem atic plot in Fig. 6. W em ake following observations: (i) the only orbitals that contribute signi cantly are pz orbitals localized on B atoms in the z=1/2 plane and Eu d_{x² y²} orbitals, (ii) at the X point the porbitals in the neighboring unit cells (in X-M direction) form a bonding orbital, which can hybridize with Eu $d_{x^2 v^2}$ orbital, going away in the X-M direction introduces a phase shift between p orbitals in neighboring cells a reduces hybridization with the d states, eventually at the M point the porbitals form an antibonding com bination and hybridization with d's is suppressed, (iii) looking along X - direction we nd that the phase shift of at X point allows the p states to hybridize with Eu $d_{x^2 y^2}$ states while this mixing is forbidden at point. In conclusion the points (ii) and (iii) explain the concave dispersion of the conduction band with bottom at the X point. The conduction band originates from the B p band which m ixes strongly with Eu d_x^2 $_{\rm V}$ $_2$ band close to the X point. This picture is corroborated by the bandstructure of the empty boron lattice (without Eu atom s) shown in Fig. 7, which contains a similar conduction band but with greatly reduced dispersion. The exchange interaction of the electrons in the conduction band with local f m om ents is of ferrom agnetic f d intra-atom ic origin. Both the reduced value of the exchange splitting

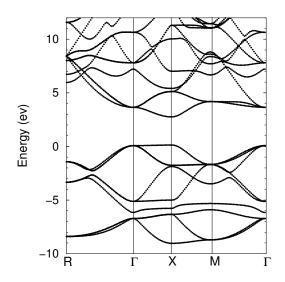


FIG. 7: The band structure of empty boron cage. The correct lling (2 additional electrons per octahedron) was achieved by virtual crystal approach.

as com pared to higher lying d-bands and decrease of the exchange splitting when going away from X point are easily explained by variable content of the Eu d in the conduction band states as described in (ii) and (iii).

C. Role of P ressure and U

In the previous section we have shown that the mechanism of exchange with the local f moments is rather di erent for conduction and valence electrons. The conduction electrons are polarized through intra-atom ic exchange interaction between the Eu d and f states. The strength of the interaction is determ ined mostly by the content of the d orbital in a particular wavefunction and is independent of the energy of f states. The polarization of valence electrons arises from di erent hybridization splitting in spin-up and spin-down channel. Since the hybridization is negligible in the minority channel, the strength of the e ective exchange is determ ined by hybridization shift of the majority valence states. This shift is inversely proportional to the energy di erence between the f and valence band. The position on the energy scale of the f states is therefore crucial for determ ining the strength of the e ective exchange.

The position of the lower and upper 4f bands is determ ined by two factors within the LDA + U approach: (i) the center of gravity of the LDA f bands, (ii) the screened on-site C oulom b interaction U. The center of gravity of the f bands depends on charge transfer, but its LDA position su ers from well-known self-interaction error. The additional term s in the LDA + U ham iltonian enforce the splitting into lower and upper H ubbard band and in an approxim ateway correct for the self-interaction error in the lower band. To calculate the precise value of

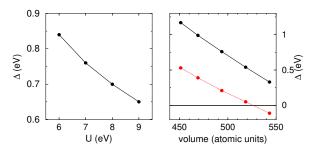


FIG.8: The band overlap of the spin-up bands as a function of the parameter U evaluated at the experimental volume is shown in the left panel. The band overlap in the spin-up channel (upper curve) and spin-down channel (lower curve) as a function of unit cell volume evaluated at U = 7 eV.

U, besides the fact that it is de ned in a som ewhat bose sense, is beyond the scope of this work. The typical U quoted for 4f electrons after accounting for screening is between 7 and 9 eV. In Fig. 8 we show the band overlap in the majority spin channel as a function of U from 6 to 9 eV. We point out that U around 7 eV yields the f bands approximately 1 eV below the Ferm i level, which is the position deduced from optical experiments²³ and therefore we assume the results for this value to be most realistic.

The e ect of applied pressure amounts to overall broadening of the bands and thus enhanced overlap of the conduction and valence bands at the X point. For a unit cell volum e increase of about 10% a gap in the m inority spin channel opens, while an appreciable overlap remains in the m a prity spin channel (see Fig. 8).

D. M odel H am iltonian

In the previous sections we have described the origin of dispersion and e ective exchange coupling with local f m om ent in both valence and conduction bands. Based on the band structure we suggest the following m odel ham iltonian to provide a reasonable description of the low energy physics:

$$H = \sum_{k=1}^{K} \sum_{k=1}^{v} v_{k}^{v} v_{k} + \sum_{k=1}^{c} c_{k}^{v} c_{k}$$

$$\frac{1}{L} \sum_{i;k=1}^{k;} J_{i;k=1}^{v} S_{i} \sum_{k=1}^{v} v_{k=1} + (1)$$

$$J_{i;kk^0}^c S_i \overset{v}{k} Q_{k^0}$$
;

where operators v_k and c_k correspond to valence and conduction bands respectively, S_i is a total spin operator of the local f m om ents and L is the num ber of unit cells in the norm alization volum e.

O btaining parameters of the model ham iltonian from the bandstructure is not a straightforward task, in particular the choice of the reference non-interacting state is tricky. It was shown by Schiller and Nolting²⁴ and further discussed by M uller and Nolting²⁵ that in case of k-independent exchange parameter J, the majority-spin band is rigidly shifted with respect to its non-interacting counterpart, while the minority-spin band is modied beyond the rigid shift due to interaction with the local moments. The situation in EuB₆ is more complicated since, as discussed below in detail, the exchange parameter is strongly k-dependent for purely chemical reasons (hybridization). It is therefore not possible to distinguish unambiguously the deviation of the exchange splitting

(k) from a rigid band shift arising from the correlation e ects in the m inority-spin band from that originating in the 'chem ical' k-dependence of the exchange param eter J. Since the k-dependence of the exchange splitting (k) along the X - and X - M directions is very pronounced and can be qualitatively understood in term s of k-dependent exchange param eter J we neglect the correlation e ects in the m inority spin channel.

The non-interacting dispersion relations ${}^{v}_{k}$ and ${}^{c}_{k}$ obtained from the bandstructure (Fig. 2) are considered separately. The interaction of the conduction electrons with the localm om ents is dom inated by the f d intra atom ic exchange depending only on the d content in a particular conduction state. The 'non-interacting' conduction band is then approxim ated by an average of the spin-up and spin-down bands. Since the hybridization in the majority band is the source of the exchange splitting in the valence band, the 'non-interacting' valence band is well approxim ated by the spin-down band. The Ferm i level is located close to the top, resp. bottom, of the valence, resp. conduction, band and so the low energy bandstructure can be param etrized by an isotropic e ective masses and the band overlap. The e ective mass tensor for an ellipsoid of revolution is characterized by only two independent parameters $_{?}$ and $_{k}$ corresponding to X-M and X- dispersion respectively. The e ective masses obtained by parabolic t from the bandstructure (Fig. 2) are $\frac{c}{2} = 0.23$, $\frac{c}{k} = 0.47$, $\frac{v}{2} = 0.25$, and $_{k}^{v} = 22$. The band overlap of the 'non-interacting' bands at X point is 0.34 eV.W e point out that using the spin-up conduction band as a non-interacting reference (rigidly shifted) does not lead to signi cant m odi cation of the e ective m asses.

Since the mechanisms of e ective exchange with local moments are di erent we have to discuss determ ination of the corresponding coupling constants $J_{i;k\,k^0}$ separately. The kk^0 dependent coupling constants can not be determined directly from the bandstructure and additional assumptions must be made. We start with the conduction band.

W e mentioned earlier that the conduction band coupling to the local moment is mostly due to intra-atom ic f d exchange described by

$$H_{df} = J S_{i} \overset{V}{\not q} d_{i}; \qquad (2)$$

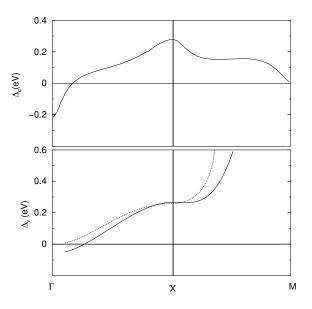


FIG.9: The k-dependent exchange splitting: splitting of the conduction band is shown in the upper panel, the splitting of the valence band is shown in the bottom panel. The exchange splitting calculated with the tight-binding expression for $V_{\rm fp} = 24$ meV is marked with the dotted line.

which leads to

$$J_{i;kk^{0}} = Je^{i(k k^{0})R_{i}}$$
 (3)

However, the conduction band is not a pure d-band, but contains a m ixture of d and p orbitals $q_k = (k)d_k +$

(k) p_k . Treating H $_{\rm df}$ as a $\,$ rst order perturbation leads to an elective coupling of the conduction of the form

$$J_{i;kk^{0}}^{c} = J e^{i(kk^{0})R_{i}} (k) (k^{0}):$$
(4)

Here can be chosen at convenience as real and positive. Finally we make connection to the band structure by observation that the k-dependent exchange splitting of the conduction band is given by

$$^{c}(\mathbf{k}) = {}^{c}_{\mathbf{k}\#} {}^{c}_{\mathbf{k}"} = 2 \mathrm{JS}^{2}(\mathbf{k})$$
: (5)

Finally putting (4) and (5) together we obtain

$$2S J_{i;kk^{0}}^{c} = e^{i(k k^{0})R_{i}} e^{-c(k) c(k^{0})}$$
(6)

The k-dependent exchange splitting of the conduction band is shown in Fig. 9. Vanishing of the exchange splitting when the and M points are approached can be understood in terms of simple nearest neighbor (NN) hopping picture. The k-dependent hybridization between p and d bands vanishes at and M, and thus the valence states have a pure p character at these points. The p d NN hopping in the conduction band has the same symmetry as the p f hopping in the valence band leading to the same k-dependence of the hybridization (9) and (10) discussed below. For the valence band the elective exchange coupling arises by Schrie $er\{W \text{ ol transform ation}^{26} \text{ from Anderson lattice ham iltonian with the f phopping term}$

$$H_{pf} = \sum_{i,k,j}^{X} V_{ik} f_{i}^{y} v_{k} + h c:$$
 (7)

The corresponding exchange parameter for states close to the Fermilevel (i.e. far enough from the f band) is given by

$$J_{ijkk^{0}}^{v} = \frac{1}{2} V_{ki} V_{ik^{0}} \frac{1}{k} + \frac{1}{k^{0}} \frac{1}{k} + \frac{1}{$$

where f is the energy of the occupied f states and f + U is the energy of the unoccupied f states. As in the case of the conduction band we have to make additional assum ption in order to extract inform ation about $J_{i;kk^0}^{v}$ from the bandstructure. The natural assumption in terms of the local orbitals is to expect non-zero hopping $V_{\rm fp}$ only between the nearest neighbor p and f (xyz) orbitals (see Fig. 4). Note that the sign of $V_{\rm fp}$, given by symmetry of the orbitals, is di erent for di erent pairs of orbitals (each p orbital solutions and for the sign for pairs connected by a vector (m;n;1=2) have the same sign, which is opposite to the sign for pairs connected by (m;n; 1=2). Now we can write down the matrix element V_{ki} as

$$V_{ik} = 2 \frac{V_{fp}}{P} e^{ik R} (k);$$
 (9)

where

$$F(k) = \sin \frac{ak_{x}}{2} + \frac{ak_{y}}{2} + \frac{ak_{z}}{2} + \frac{ak_{z}}{2} + \frac{ak_{x}}{2} + \frac{ak_{x}}{$$

P roviding we know the value of the hopping parameter $V_{\rm fp}$ the coupling $J^v_{j,k\,k^0}$ can be calculated by feeding the above expression and the known dispersion relation into equation (8). In order to obtain the parameter $V_{\rm fp}$ we express the exchange splitting of the valence band as

$$v(\mathbf{k}) = v_{\mathbf{k}''} \quad v_{\mathbf{k}\#} = 8SV_{fp}^2 F(\mathbf{k})^2 \frac{1}{\mathbf{k} + f} \frac{1}{\mathbf{k} + f + U}$$
(11)

and use the fact that along the -X direction F (k) = $4 \sin(ak_z=2)$, while along the X-M direction F (k) = $4 \cos(ak_x=2)$. The exchange splitting of 0.26 eV and $_k$ f leV at the X point yield $V_{\rm fp}=24$ meV. In Fig. 9 we show the k-dependent exchange splitting together

with the expected k-dependence. For the X-M direction we show only the region close to the Ferm i level. The reason is that close to the crossing of the non-interacting band with the f level the exchange splitting (k) is not well de ned.

E. M ean eld results

Here we want to illustrate the potential usefulness of the suggested ham iltonian by investigating some of its – nite temperature properties in mean eld approximation. Due to the three dimensionality and the large moment, mean eld should be realistic in many respects. A similar approach was taken by K orenblit⁴ without providing detailed results. We focus on the role of the exchange enhanced band overlap and its consequences. In the mean eld approximation the ham iltonian (1) reduces to

$$H_{MF} = \begin{cases} X & X \\ k & v_{k}^{y} & v_{k} + c_{k}^{z} & c_{k}^{y} & c_{k} \end{cases}$$
 (12)

where the spin-dependent dispersion relations are given by ${}^{a}_{k} = {}^{a}_{k} J^{a}hS^{z}i$ and $h = {}^{a}J^{a}(n^{a}_{*} n^{a}_{\#})$ is an e ective self-consistent magnetic eld, with a = v;c and = 1. The quantities $n^{a}_{*};n^{a}_{\#}$ are the occupations of the bands. G oing to the hole picture of the valence band and using the charge neutrality condition to determ ine the Ferm i level we obtain the follow ing set of equations

X
$$n_{c} (S^{z}) n_{v} (S^{z}) = 0$$
 (13)

$$h = J^{c}n_{c} (S^{z}) J^{v}n_{v} (S^{z})$$
(14)

$$S^{z} = B_{7=2} \frac{h}{k_{\rm B} T}$$
; (15)

where $B_{7=2}$ (x) is the Brillouin function for S = 7=2.

We have solved the mean eld equations using the effective m asses listed above. To make the analysis as sim – ple as possible we approximate the coupling parameters J with a single k-independent constant (with opposite sign for the valence and conduction bands). To assess sensitivity of the model to the choice of J, we have used two values: (i) jJ j = 0.04 eV corresponding to the X point exchange splitting of 0.28 eV (see Fig. 2) and (ii) jJ j = 0.10 eV used by K orenblit.⁴ The calculated ordered moment vs. tem perature S_z (T) curves are shown in Fig. 8. There are two distinct regimes.

(i) For band overlap < 0 (i.e. bandgap of j) there is a minimum ordered moment $S_{m in}$ necessary to establish the overlap of spin-up bands. Below this value the magnetization cannot be self-stabilized since the corresponding e ective eld h is zero. Solution of equation (15) can be visualized as the intersection, on the interval (0,7/2], of the right-hand side $s = B_{7=2}$ as a function of S^z , given by (14), and the straight line $s = S^z$ of the left-hand side. The right-hand side is zero for $S < S_{m in}$ and, from de nition of B₇₌₂ (x), less or equal to 7/2. This means that curve representing the right-hand side must cross the line representing the left-hand side an even number of times since it is continuous and its initial and nalpoints are in the same half-plane determ ined by the left-hand side. Therefore there must be an even number of non-zero solutions of (15) for < 0 and a given tem perature. In our case it means either zero or two solutions.

In order to identify, in the two solution case, the solution with lower free energy we approximate the total free energy by the sum of the free energy of non-interacting valence and conduction electrons evaluated with the selfconsistent value of the electric eld h and the free energy of non-interacting local moments in the electric eld h at a given temperature. In all cases we not that the solution with larger ordered moment corresponds to the lower free energy.

The ham iltonian (1) preserves separately the number of electrons in valence and conduction bands. If those bands are completely lled or empty in the noninteracting ground state, which is degenerate with respect to orientation of the local moments, there is no e ective coupling between the local moments since the degenerate grounstate manifold is disconnected from the excited states. On the other hand when a minimum net m agnetization already exists a band overlap is induced and a magnetic groundstate can be found as described by the mean eld equations. There is no continuous connection between the non-magnetic and magnetic states and therefore we conclude that the transition is of the rst order.

(ii) For > 0 one solution exists in most of the studied cases, with the ordering temperature increasing as

increases. The magnetization versus tem perature behavior deviates from the standard W eiss curve, which is obtained for linear dependence of the e ective eld h on S_z . In a narrow range of close to zero three solutions may exist, providing yet another phase transition below the magnetic (nonmagnetic one. W e do not make any conclusions about the order of the phase transition in this parameter range. In the insets of F ig. 8 we show the ordering tem peratures as a function of band overlaps. The di erence between the ordering tem peratures obtained with di erent coupling constants J indicates a strongly non-linear T_c vs. J dependence. (N ote that if the band shifts due to the ordering of the localm om ents are very small, $T_c / J^2 \operatorname{Ref. 4}$).

IV. D ISCUSSION

O ne of the controversial questions concerning divalent alkaline earth hexaborides is whether the groundstate is insulating or m etallic at stoichiom etry. The experim ental as well as theoretical evidence is controversial. Recent LDA calculations by M assidda et a^{β} neglecting the m agnetic order yield a m etallic band structure for EuB₆

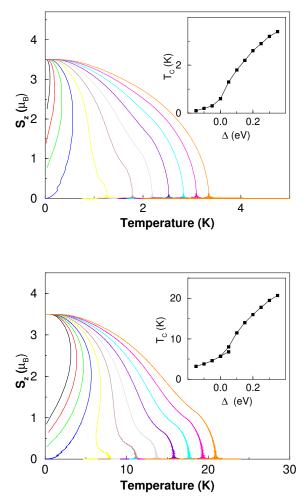


FIG.10: O rdered spin m om ent vs. tem perature evaluated from the mean-eld model for various values of the band overlap. The upper and low erpanel correspond to J=0.04 and 0.1 eV respectively. The magnetization curves, ordered from the left to the right, correspond to band overlaps from -0.15 eV (bandgap) to 0.35 eV (with a step of 0.05 eV). The ordering tem peratures as a function of the band overlaps are shown in the insets. The low er T_c for J=0.1 eV and =0.05eV correspond to the second phase transition.

sim ilar to that of C aB₆ or SrB₆ with a sm all band overlap of about 0.3 eV. The selfconsistent GW calculation¹² nds C aB₆ to be a sem iconductor with a band gap of the order of 1 eV, as does the more conventional pseudopotential GW calculation.¹⁰ The GW method is known to provide good bandgaps for many sem iconductors where the LDA gaps are strongly underestimated or even vanishing. The elect of GW self-energy corrections on the EuB₆ bandstructure is expected to be similar, thus reducing the band overlap and possibly opening a band gap by shifting the conduction band upwards.

A n important di erence between $E uB_6$ and $C aB_6$ is the presence of 4f orbitals. We have show n that the exchange interaction with the band electrons is opposite in sign for the valence and conduction bands, so m agnetic order

can signi cantly increase the overlap of the majority spin band while it has opposite e ect for the minority spin. A lthough the elective exchange with the valence band depends on the position of the 4f states and thus varies som ewhat with the parameter U, general experience with rare earth systems as well as optical measurements on ${\rm EuB_6}^{23}$ indicate that U of 7 eV (placing the Eu 4f 1 eV below the Ferm i level) is realistic.

B ased on these arguments it is plausible that the realistic ground state picture of stochiom etric EuB_6 is that of a half m etallic sem in etal. This unprecedented band structure would result from a ferrom agnetic GW calculation in which the band shifts (relative to the static LDA + U) are large open a gap in the m inority spin channel, but not so large as to open a gap in the m a prity spin channel. Such a scenario has some experimental support. de H aas{van A lphen data provide clear indication of Ferm i surfaces, but only two pockets are seen.^{27,28} This num – ber of sheets is contrary to the expected four pockets suggested by LDA (and LDA+U) band structure, but two sheets are exactly what is expected of a half m etallic sem in etal.

The observed behavior of the resistivity is also consistent with such a picture. In the magnetically ordered state, metallic conduction takes place in the majority spin channel. Just above the magnetic ordering tem – perature the system can be viewed as consisting of disordered magnetic domains (due to short range ferrom agnetic correlations), and the increase of resistivity upon disordering is due to m ism atch of the conducting spin channels between these domains (like the \intergrain tunneling mechanism " of giant magnetoresistance materials; see e.g. Ref. 29). Increasing the temperature further leads to breakdown of the short range order, the paramagnetic bandstructure becomes increasingly appropriate, and the inter-domain magnetoresistance e ect disappears, as observed.

A ngle-resolved photoem ission data¹³ do not seem to t well into this picture, but further photoem ission studies in the ordered phase, and identifying the position and in uence of the f states, seem s to be necessary to clarify several remaining questions. The very large number of electron carriers that the photoem ission data, if assumed to be representative of the bulk, does not t so well with data that suggest rather clean single crystals. If the carriers are due to unbalanced surface charge, then the observed bands are not representative of the bulk. Finally, the broken inter-octahedron B-B bonds should give rise to surface states (or bands), and the im plication of the photoem ission data will never be unam biguous until the surface electronic structure is identi ed and understood.

F inally we discuss brie y our mean eld treatment of the two band K ondo lattice model ham iltonian. We expect that the least reliable quantity obtained from the electronic structure calculation is the band overlap, and we have treated it as a parameter in the mean eld study. The two band ham iltonian even in mean eld approxim ation leads to a strongly temperature dependent coupling between the localm om ents, which is relected by unusual magnetization dependences distinct from the canonical behavior of the Heisenberg ham iltonian in mean eld. The solutions for small positive band overlap exhibit a slow approach to saturation as observed, 5 as well as an increase of the ordering tem perature with pressure,⁶ i.e. with increasing band overlap. The ordering tem peratures obtained with the ab inito value of the exchange param eter J are, however, too low compared to experiment. W emention several possible reasons for this discrepancy. First, we have completely neglected the k-dependence of the exchange parameter J. Second, equation (8) shows that the value of J^{v} is quite sensitive to the position of the occupied 4f levels, which we know only approximately. And nally, some mechanisms of e ective exchange between the local m om ents arising from the Anderson model are lost when transformed to the Kondo model (e.g. superexchange). These mechanisms might be of importance in the < 0 case leading to rem oval of the rst order transition. The mean eld study does serve to dem onstrate the potential usefulness of the two-band ham iltonian and to stimulate further studies by more advanced techniques, such as the G reen's function approach of Nolting et al.30

V. CONCLUSIONS

Using the LDA + U approach we have shown that treating the Eu 4f states within the same framework as the rest of the itinerant electrons has in portant consequences. In particular it leads to K ondo coupling between local moments and valence electrons, but anti-K ondo coupling to conduction electrons. W e have identi ed and described in detail the origin of this coupling as well as the origin of the k-dependence of the anti-K ondo (ferrom agnetic) coupling to the conduction band. Based on our electronic structure analysis we suggest the description of EuB₆ in terms of two band K ondo/anti-Kondo lattice model, and shown that a half metallic sem in etal results at the mean eld level of description. W e have obtained the param eters of the corresponding ham iltonian, which will allow more extensive materialspecic treatments in the future, and demonstrated the e ects on magnetic ordering arising from an exchange controlled band overlap. The picture we present seems consistent with observed Ferm i surfaces and transport properties.

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